

IRLM110A-VB Datasheet N-Channel 100-V (D-S) MOSFET

PRODU	CT SUMMARY	
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)
100	0.100 at $V_{GS} = 10 \text{ V}$	5.0
100	0.120 at V _{GS} = 4.5 V	4.5

FEATURES

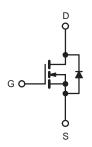
 Halogen-free According to IEC 61249-2-21 Definition



RoHS COMPLIANT

- Trench Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}		100	V	
Gate-Source Voltage		V_{GS}	±	20		
Continuous Drain Current (T _{.1} = 175 °C) ^a	T _A = 25 °C	l _n	5.0	4.5		
Continuous Diain Current (1) = 175 C)	T _A = 70 °C	ΙD	3.5	3.0	Α	
Pulsed Drain Current		I _{DM}	:	25	^	
Avalanche Current		I _{AS}		15		
Single Pulse Avalanche Energy		E _{AS}		11	mJ	
Manianum Danum Disainationa	T _A = 25 °C	P _D	P_ 3.3	1.7	W	
Maximum Power Dissipation ^a	T _A = 70 °C	• В	2.3	1.2	VV	
Operating Junction and Storage Temperature Ran	ige .	T _J , T _{stg}	- 55	to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana lanation to Ambient 3	t ≤ 10 s	R _{thJA}	36	45	
Maximum Junction-to-Ambient ^a	Steady State		75	90	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	20	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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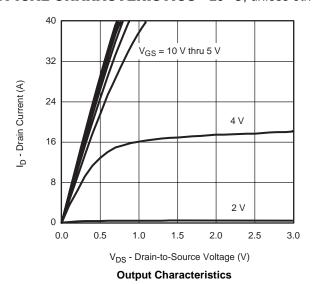
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Cata Valtana Duain Comment	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA	
Zero Gate Voltage Drain Current		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			20	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
		$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}$		0.110			
	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 4.0 \text{ A}, T_J = 125 \text{ °C}$		0.122		Ω	
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, I_D = 4.0 \text{ A}, T_J = 175 ^{\circ}\text{C}$		0.140			
		$V_{GS} = 4.5 \text{ V}, I_D = 3.1 \text{ A}$		0.120			
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 4.0 \text{ A}$		25		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			18	27		
Gate-Source Charge	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 4.0 \text{ A}$		3.4		nC	
Gate-Drain Charge	Q_{gd}			5.3			
Gate Resistance	R_g	$V_{GS} = 0.1 \text{ V, f} = 5 \text{ MHz}$	0.5	1.4	2.4	Ω	
Turn-On Delay Time	t _{d(on)}			10	20		
Rise Time	t _r	V_{DD} = 50 V, R_L = 30 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 1$ A, $V_{GEN}=10$ V, $R_g=6$ Ω		25	50	ns	
Fall Time	t _f			12	24		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 1.7 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		50	80		

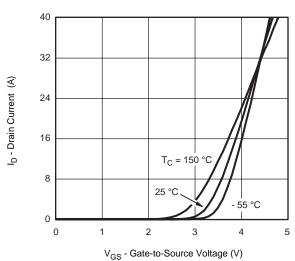
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



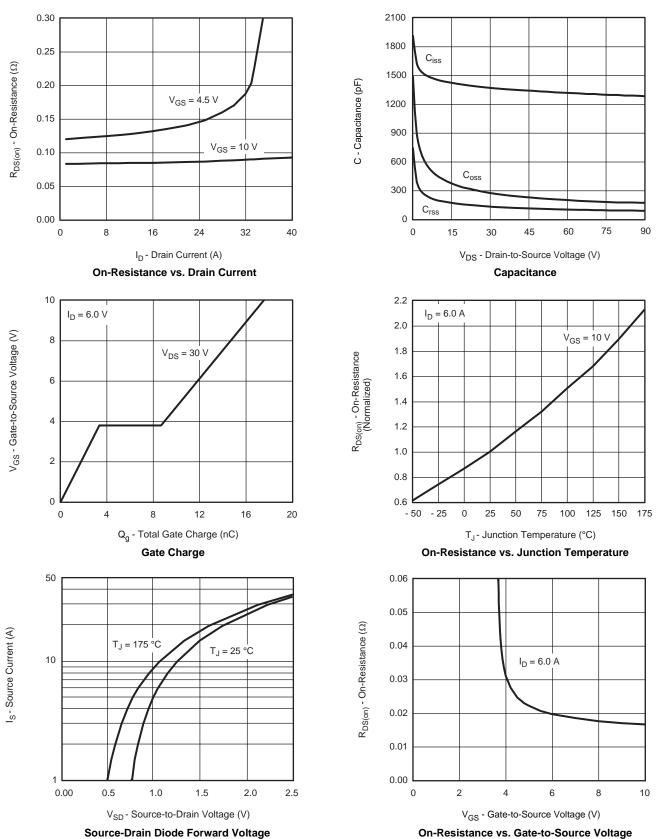


Transfer Characteristics

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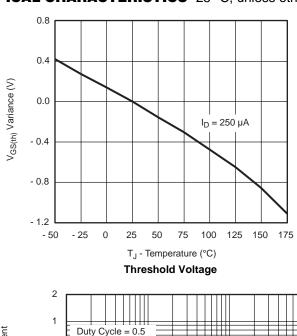
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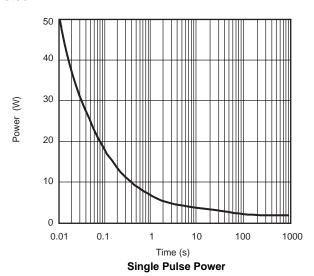


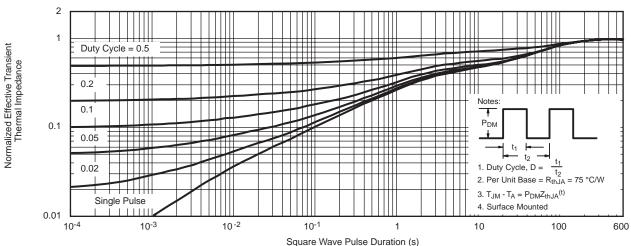
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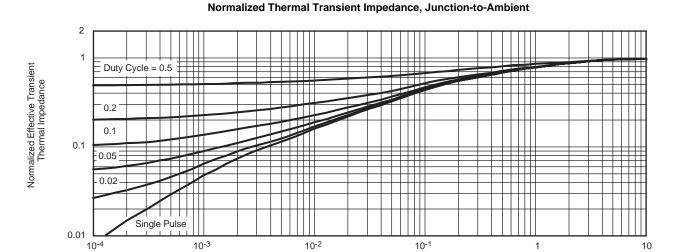


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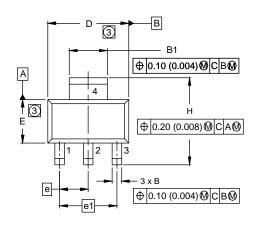


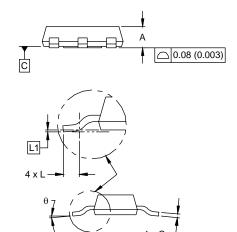
Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-223 (HIGH VOLTAGE)





DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
Α	1.55	1.80	0.061	0.071
В	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
С	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
е	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181	BSC
Н	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024	4 BSC
θ	-	10'	-	10'

ECN: S-82109-Rev. A, 15-Sep-08

DWG: 5969

Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension do not include mold flash.
- 4. Outline conforms to JEDEC outline TO-261AA.

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